

SANYO Semiconductors DATA SHEET

N-Channel Silicon MOSFET

2SK2405 — General-Purpose Switching Device Applications

Features

- · Built-in FRD.
- · 10V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		450	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	ID		10	А
Drain Current (Pulse)	IDP		40	Α
Allowable Power Dissipation	Do		1.65	W
	PD	Tc=25°C	70	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	UIIIL
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	450			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =450V, V _{GS} =0V			1.0	mA
Gate-to-Source Leakage Current	IGSS	V _{GS} = ±30V, V _{DS} =0V			±100	nA
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	2.0		3.0	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =6A	3	6		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)	I _D =6A, V _{GS} =10V		0.55	0.75	Ω
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz		1500		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		220		pF
Reverse Transfer Capacitance	Crss	V _{DS} =20V, f=1MHz		75		pF

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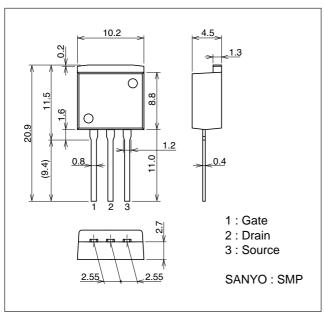
2SK2405

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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		22		ns
Rise Time	t _r	See specified Test Circuit.		60		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		230		ns
Fall Time	tf	See specified Test Circuit.		75		ns
Diode Forward Voltage	V _{SD}	IS=10A, VGS=0V			1.5	V
Diode Reverse Recovery Time	t _{rr}	I _S =10A, di / dt=100A / μs		150	195	ns

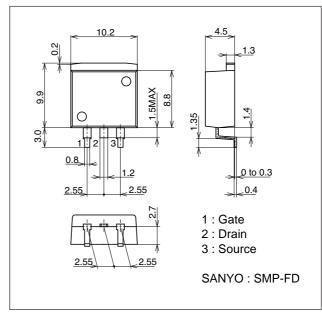
Package Dimensions

unit : mm(typ) 7513-002

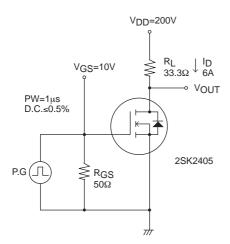


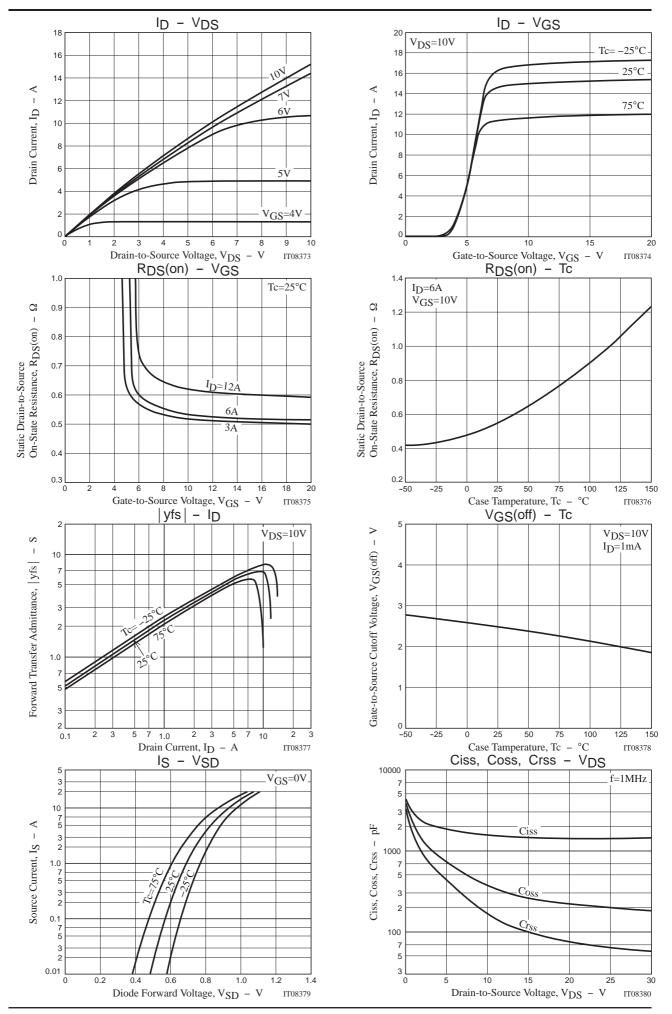
Package Dimensions

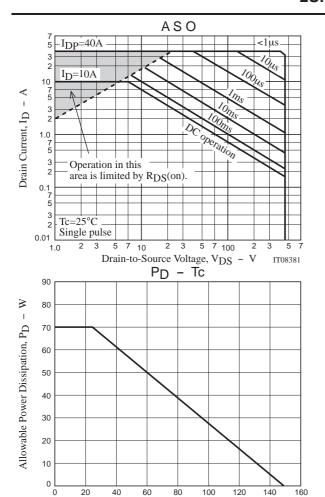
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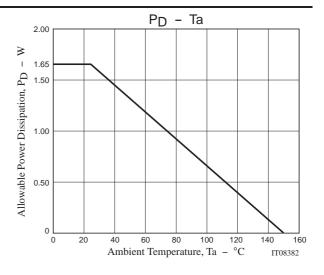
Switching Time Test Circuit







Case Tamperature, Tc - °C



Note on usage: Since the 2SK2405 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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